Calibration and Regulation of BrainScaleS' Powerlt Subsystems

Patrick Nisblé

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This Thesis will address Calibration and Regulation of the in BrainScaleS used power delivery Board, Powerlt. Its circuitry will be examined and calibrated, for use in BrainScaleS' monitoring and a method of regulating the 1.8V Output Terminal will be implemented.

This thesis also contains the changes done to the Powerlt Firmware while working on these Problems.

Diese Arbeit befasst sich mit de Kalibration und Regulation der Powerlt Komponenete des BrainScale Systems. Die Schaltungen werden untersucht und kalibriert, damit sie in der Systemüberwachung von nutzen sein können.

Ausserdem enthält diese Arbeit die Änderungen, die dabei auf die Powerlt Firmware angewendet werden.

Contents

1	Intro	oduction	3
	1.1	The BrainScale System	3
	1.2	About the Powerlt Subsystem	
	1.3		
2	The	ory	6
	2.1	Hardware Component Behavior	6
	2.2	ADC Calibration	10
	2.3	1.8V Output Regulation	
3	Expe	eriments	16
	3.1	Characterization	16
	3.2	1.8V Regulation	22
	3.3	Pitfalls	
4	Resu	ılts	31
	4.1	Firmware	31
	4.2	Calibration	
	4.3	Regulation	
5	Out	look	36

1 Introduction

1.1 The BrainScale System

The BrainScale Wafer System [1], developed and used in the electronic visions Group at Heidelberg University is a neuromorphic hardware implementation.

For this thesis the following core components are of importance:

- mixed-signal ASICs, named HICANNs, structured in packs of 8 into Reticles
- Control Units for Reticles, short CURE Boards
- analog breakout Boards, AnaB for short
- and power supply, called Powerlt.

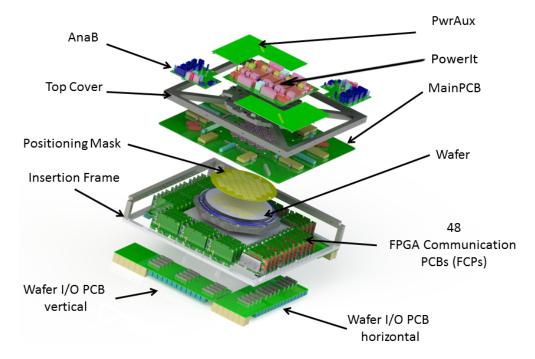


Figure 1.1: The BrainScaleS wafer-scale hardware system, marked are the main components comprising a single wafer system. [2]

1.2 About the Powerlt Subsystem

The main subject of this thesis is the Powerlt board (Figure 1.2). It functions as power supply inside of the WaferScale System (Figure 1.1). In which it is providing the Wafer with 1.8V and the FPGAs with 9.6V. Its maximum rated power draw is 2kW. [3]



Figure 1.2: Powerlt Board, top view, receiving 48V as input (top left) and outputting 9.6V (top and bottom) as well as 1.8V (analog: top left, bottom right; digital: top right, bottom left)

The Brain of these Powerlt Boards is a STM32 Chip¹ which runs a custom Firmware based on ChibiOS [5]. The Powerlt, while providing 9.6V and 1.8V, also is able to measure the following Values:

- input Voltage and current
- 1.8V output voltage and current
- and the 9.6V output Voltage

Which can then be used inside the Firmware.

¹STM32F405RGT [4]

1.3 Contents on Detail

- Upgrade the Powerlt Firmware to be able to calibrate all on board measurements, voltages and currents.
 - This requires the Firmware to handle calibration changes on the fly, (each Powerlt requires its own configuration, which needs to be changed after the Firmware is running).
- Provide a communication interface for changing those parameters at runtime.
 It is required to have write access to all coefficients (defining the degree of polynomial is done at compile time).
- Provide access to more parameters within the Powerlt while unifying the protocol used.
 Collect all writable, readable and static parameters in a single interface using PItCOMM v2, creating a mapping for reference to those values.
- Calibrate the onboard measurement circuits, using a database containing uniquely mappable values.
 - Characterizing the circuits, providing a default for fallback and a Database file, readable by the BrainScaleS Monitoring System and the Person calibrating each Board.
- Provide a regulation mechanism for stable, modifiable output at its endpoints.
 The connection between Powerlt and HICANNs can be seen as a non zero Resistance, which requires the 1.8V output to regulate based on experimental data.

2 Theory

This Chapter will be discussing the fundamental principles used in the experiments. These will contain simplified circuits and their respective Equations as well as component behavior as specified in their respective datasheets by their Manufacturer

2.1 Hardware Component Behavior

Before discussing the experimental results it needs to be clear what circuitry is used in these experiments and what behavior we expect. Keeping in mind, that these are theoretical values and will most likely not be exactly the same as those found in actual hardware, as all values given will always be within some error as defined by their manufacturer.

Each of the three voltage regimes that will be observed on the Powerlt Board, 48V 9.6V and 1.8V, has a voltage- and in the cases of 48V and 1.8V also a current-measurement circuit. Additionally we have a temperature sensor built into the STM32 Chip.

2.1.1 48V Input Voltage

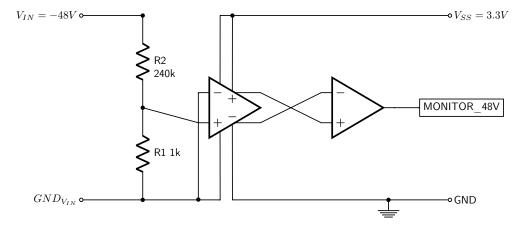


Figure 2.1: Circuit for measuring the 48V input Voltage, consisting of input potential (left), two resistors as voltage divider, one fully differential isolation amplifier (left), one operational Amplifier (right), output voltage as well as the connection to the STM32-Chips input pin (right)

The circuits for measuring input voltage and current are the most complex, because for Voltage measurement the circuit needs to

- divide our input voltage into a usable potential range
- decouple the input (48V) from signal potential (3.3V)
- amplify the voltage, to be in the STM32-Chips Voltage range of 0-3.3V

The already implemented Cicuit can be seen in Figure 2.1. It consists of a 1:240 Voltage Divider, a full differential isolation amplifier taking in the roughly 200mV (nominal voltage range), and amplifying it by a factor of 8 ($r_{\rm diffOpAmp}$ [6]). It is also decoupling the input and output voltages, so our 48V and 3.3V circuit parts are electricly insulated. The remaining operational amplifier provides difference to single ended Conversion with an amplification or 1.1 ($r_{\rm OpAmp}$)

This circuit results in the following equation for calculating the input voltage from a pin voltage:

$$V_{48V \text{ in}} \cdot \frac{R_1}{R_1 + R_2} \cdot r_{\text{diffOpAmp}} \cdot r_{\text{OpAmp}} = V_{\text{MONITOR}_48V}$$

$$\Leftrightarrow \frac{V_{\text{MONITOR}_48V}}{r_{\text{diffOpAmp}} \cdot r_{\text{OpAmp}}} \cdot \frac{R_1 + R_2}{R_1} = V_{48V \text{ in}}$$
(2.1)

and the extremes, when assuming $48V\pm10\%$ are

$$V_{\text{MONITOR_48V, min}} = 43.2 \,\text{V} \cdot \frac{1}{240+1} \cdot 8 \cdot 1.1 = 1.5774 \,\text{V}$$
 (2.2)

$$V_{\text{MONITOR_48V, max}} = 52.8 \,\text{V} \cdot \frac{1}{240+1} \cdot 8 \cdot 1.1 = 1.9280 \,\text{V}$$
 (2.3)

2.1.2 48V Input Current

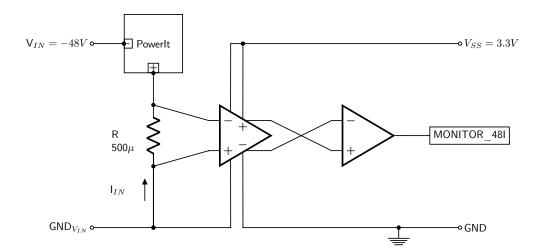


Figure 2.2: Circuit for measuring the 48V input Current, consisting of the powerit Input Circuit, one shunt-resistor, one full diff isolating Amplifier, one operational amplifier, output potential, as well as the connection to the STM32-Chip input pin

In case of the current measurement circuit we require the following:

- 1. use a shunt resistor, with minimal heat dissipation
- 2. still providing a good resolution also within the Chips Specifications

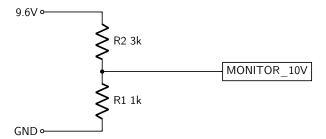
Here we use the same Amplifiers and so we can use the following equation for our input current:

$$I_{48V \text{ IN}} \cdot R_{\text{shunt}} \cdot r_{\text{diffOpAmp}} \cdot r_{\text{OpAmp}} = V_{481 \text{ pin}}$$

$$\Leftrightarrow \frac{V_{481 \text{ pin}}}{R_{\text{shunt}}} \cdot \frac{1}{r_{\text{diffOpAmp}} \cdot r_{\text{OpAmp}}} = I_{48V \text{ IN}}$$
(2.4)

2.1.3 9.6V Output Voltage

This Circuit consists of a a simple 1:4 Voltage Divider.



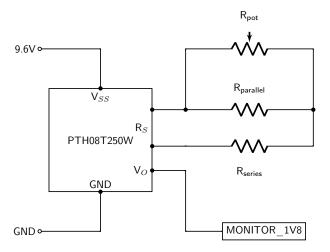


Figure 2.3: Circuit for generating a changable Output Voltage, consisting of the DC-DC Converter, a resistor chain, supply voltage (left) and resulting voltage (right)

And the following equation shows that:

$$V_{10V \text{ PIN}} = \frac{V_{10V \text{ IN}} \cdot R_1}{R_1 + R_2} \tag{2.5}$$

2.1.4 1.8V Output Voltage

until now the voltages and current could only be measured, now the mechanism for setting a resulting Voltage at the 1.8V Terminals is known. Figure 2.3 is the circuit for generating 1.8V, it consists of a power module and a resulting resistance at given pind, defined by R_{series}, $R_{parallel}$ and R_{pot} , whose job is to set the output to a given voltage of around 1.8V, but we can vary R_{pot}, because this resistance is set vie a digital potentiometer.

The in Figure 2.3 used 1.8V Converters have a characteristic formual [7], and the in this circuit used Potentiometer is a linear $10k\Omega$ Rheostat resulting in the following equations:

$$R_{potentiometer} = P_{val} \frac{10k\Omega}{256}$$

$$R_{SET} = 1/\left(\frac{1}{R_{potentiometer}} + \frac{1}{R_{parallel}}\right) + R_{series}$$

$$= \frac{R_{potentiometer} \cdot R_{parallel}}{R_{potentiometer} + R_{parallel}} + R_{series}$$

$$V_O = \frac{30.1k\Omega}{R_{SET} + 6.49k\Omega} \cdot 0.7V + 0.7V$$
(2.8)

$$R_{SET} = 1/\left(\frac{1}{R_{potentiometer}} + \frac{1}{R_{parallel}}\right) + R_{series}$$

$$= \frac{R_{\text{potentiometer}} \cdot R_{\text{parallel}}}{R_{\text{potentiometer}} + R_{\text{parallel}}} + R_{\text{series}}$$
 (2.7)

$$V_O = \frac{30.1k\Omega}{R_{SET} + 6.49k\Omega} \cdot 0.7V + 0.7V \tag{2.8}$$

This equation is in contrast to all previous behavior models not of a linear nature but proportional to $\frac{1}{x}$ as visualized in Figure 2.4

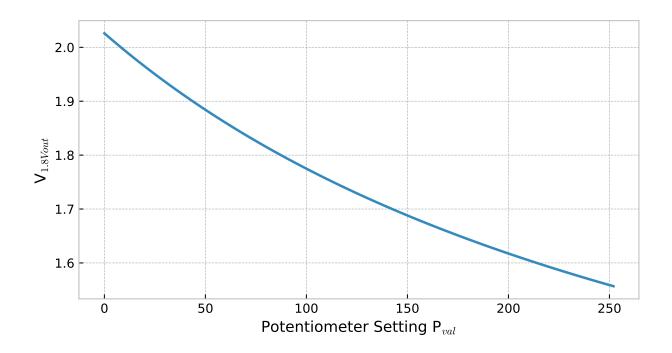
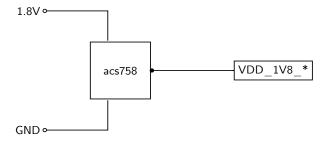


Figure 2.4: Expected behavior of our output voltage by setting the potentiometer

2.1.5 1.8V Output Current

The circuit for measuring current is also quite straight forward. It consists of a current sensing IC, which is Hall sensor based, and is in series with the wafer connection. One each for digital and analog.



2.2 ADC Calibration

As mentioned beforehand, the actual hardware will differ in behavior from its theoretical counterpart. These discrepancies will in fact differ by more than we can accept and use

without countermeasures. Therefore we can say that all signals with a signoficant difference of behavior ($\approx 5\%$) will need to be corrected.

To calibrate these readouts we need to employ some simple actions.

2.2.1 serial ADC readout

While the measurements done by the STM32-Chip are using a 12bit ADC, there are not enough of these inside the chip to be able to completely parallelize the measurements, so only one ADC will be switching between all connected pins. This Behavior can be problematic in regards to measuring accurately. The timing used to measure a single line can be programmatically set from 3 up to 480 clock ticks¹

2.3 1.8V Output Regulation

For Regulting the Output the method used is a numerical one, we calculate the voltage wanted at the putpu terminal and then we calculate a potentiometer setting, which changes the voltage produced (see Figure 2.3). The second part is already done beforehand and then available as lookup table to the firmware. On the other hand, to calculate the voltage to ouput, it is necessary to classify the connections between the Powerlts ouput terminals and the reticle.

2.3.1 Power Wafer

To test the 1.8V Regulation the so called Power Wafer is going to be used, it bahves similarly to a in BrainScales used "fuctional" Wafer module. But it is fundamentally different, as it cannot be used for computation, but only to test for voltages and currents. Its internals behave like switchable ohmic resistors, which provides us with a maximum powerdraw per Reticle of what is possible inside a usable wafer module.

¹this clock is the internal adc clock, with a frequency of

			0	1	2			
		3	4	5	6	7		
	8	9	10	11	12	13	14	
15	16	17	18	19	20	21	22	23
24	25	26	27	28	29	30	31	32
	33	34	35	36	37	38	39	
		40	41	42	43	44		
			45	46	47		•	

Figure 2.5: reticle diagram of a wafer in BrainScaleS, orientation as used in software and to better visualize connections on the wafer. All 48 Reticles are shown, all numbered from top left to bottom right

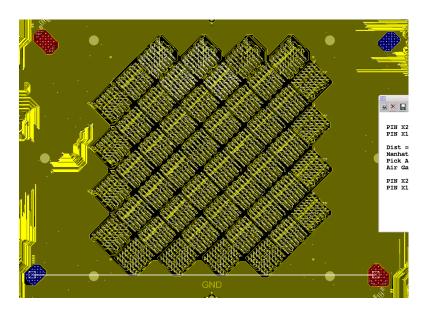


Figure 2.6: part of the mainpcb on which a wafer is placed, in its realworld orientation (rotated 45° from Figure 2.5), visible are the 48 Reticles and two terminals each for 1.8V Digital (blue) and Analog (red)

It has the same layout as its system counterparts and each of the 48 Reticles can be accessed, digitaly as well as electricaly. Each Reticle is connected to its corresponding CURE Board, which can read voltages of each reticle, right after the PowerFETs, reponsible for switching on power to a Reticle (switches in Figure 2.7)

Another specialization of the Power wafer is, that all reticles voltages are connected directly to pins on the Analog Readout Boards [8]. There it is possible to measure a voltage, which is the one after the load resistors in Figure 2.7

2.3.2 Simple Wafer Resistance Model (SWRM)

The circuit in Figure 2.7 can be used, as a first step, to describe the connections powering Reticles inside a wafer.

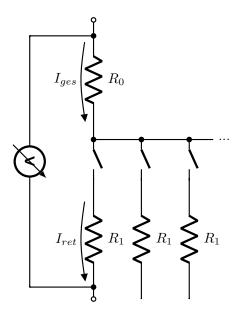


Figure 2.7: model of the to measure resistances and their currents, R_0 describes the resistance of a connection between the Powerlt Output and up to the FET, while R_1 is a Resistance between FET and Reticles. The measurement is done between Output Terminals on the Powerlt and pins on a Analog readout board

SWRM allowes for two fixed resistance values and their respective currents. The current flowing through R_1 will be either 0 or a constant current I_{ret} . The current through R_0 will change depending on the number of reticles that are powered n_{ret}

$$I_{ges} = n_{ret} \cdot I_{ret} \tag{2.9}$$

Therefore the voltage Differential as measured by a Voltmeter (see Figure 2.7) can be described with Equation 2.10

$$V_{dip} = V_{R_1} + V_{R_0}$$

$$= R_1 \cdot I_{ret} + R_0 \cdot I_{ges}$$

$$= I_{ret} \cdot (R_1 + R_0 \cdot n_{ret})$$
(2.10)

Combining Equations 2.6, 2.7, and 2.8, we gather Equation 2.11. This equation is a reversed function of the one used in Figure 2.3

$$P_{val} = \frac{R_{par} \left[\left(\frac{0.7V \cdot 30.1k\Omega}{V_O - 0.7V} - 6.49k\Omega \right) - R_{ser} \right]}{R_{par} + \left(\frac{0.7V \cdot 30.1k\Omega}{V_O - 0.7V} - 6.49k\Omega \right) - R_{ser}} \cdot \frac{256}{10k\Omega}$$
(2.11)

inside the code used for Regulation, Equation 2.11 will be used to create a lookup table, while Equation 2.13 will be used at runtime, for which Equation 2.10 and 2.12 are needed.

$$V_{dip} = V_O - V_{off} \tag{2.12}$$

$$\Rightarrow V_O = I_{ret} \cdot (R_1 + R_0 \cdot n_{ret}) + Voff$$
(2.13)

2.3.3 Distance Wafer Resistance Model

Although the through SWRM gained functions are useful for determining a theoretical Regulation procedure, it is still not near the realworld scenario. In a wafer, the distance between reticles and voltage connector (see Figure 2.6) are resulting in additional resistance, proportionally.

Therefore we adapt the DWRM after Circuit 2.8 in which each different Distance requires additional Resistors.

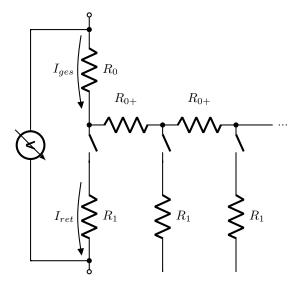


Figure 2.8: retpow2

With this model the voltage is now expected to change depending on the reticles distance instead of being the same. The distances inside a wafer are visualized in Figure 2.9

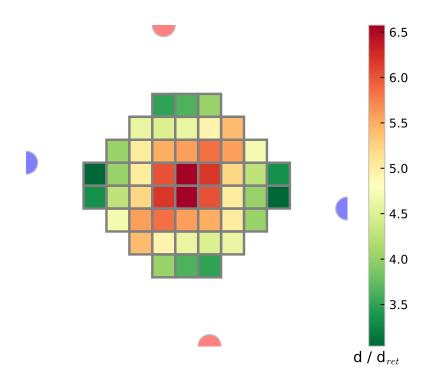


Figure 2.9: Distances of reticles to the nearest voltage supplying connection for DWRM, distance is in reticle-side length

3 Experiments

Now that the theoretical model sicomplete, experiments can be done to start checking that model and get results to use for in system components.

3.1 Characterization

The first experiments to run are the caracterization of hardware behavior. These will then result in a Powerlt Calibration, which later then can be used as basis for creating a regulation method.

3.1.1 sampling time

First up was selecting an optimal number of cycles for which the adc will probe a to it connected pin, like described in subsection 2.2.1.

In this case the uncalibrated measurement of input voltage was taken as example, and repeated with each of the possible 8 settings.

To be able to compare a reference voltage measurement was taken with an external Voltmeter. The resulting errors, from a set Voltage, can be seen in figures 3.1

Figure 3.1 contains the relative error of the measured voltage compared to the theoretical, set input voltages. therefore the reference measurements (yellow), taken with an external multimeter, are not at 0. Also shown are the calculated gain errors, in case of all 8 settings.

Important to note is the relative error in only the 0th case, here the <code>cycleTime-Setting</code> was set to 0 and therefore the smallest available sampletime of 3 Ticks. This excludes 0 a possible value to use. All other measurements are within errormargin of each other, and because a smaller timeframe is preferred, the best value to use is 1, resulting in a measuretime of 15 Ticks.

3.1.2 Voltages

Now that a sampleTime is chosen, it is possible to proceed with the voltage calibration measureemnts. Note, that Measuremts are expected to be less accurate, the more components are contained in their respective measurement circuit. Because small errors will accumulate and in e.g. the case of 48V's be amplified by a factor of 8.

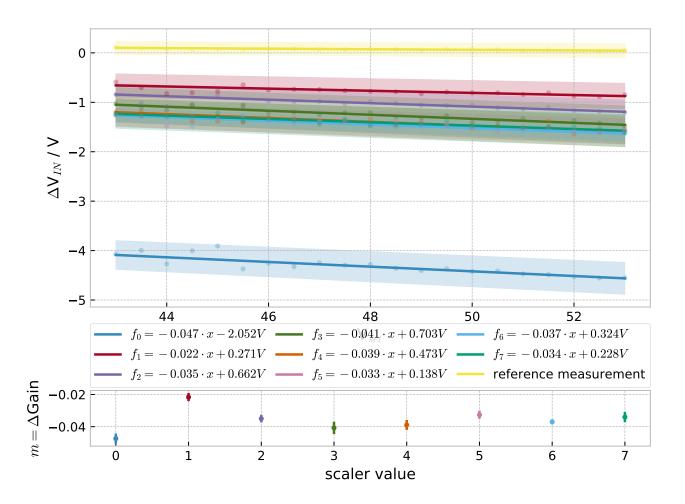


Figure 3.1: plotted difference from set input voltage, and fitted linearly, May 29th 2018, ${\approx}32^{\circ}\text{C}$

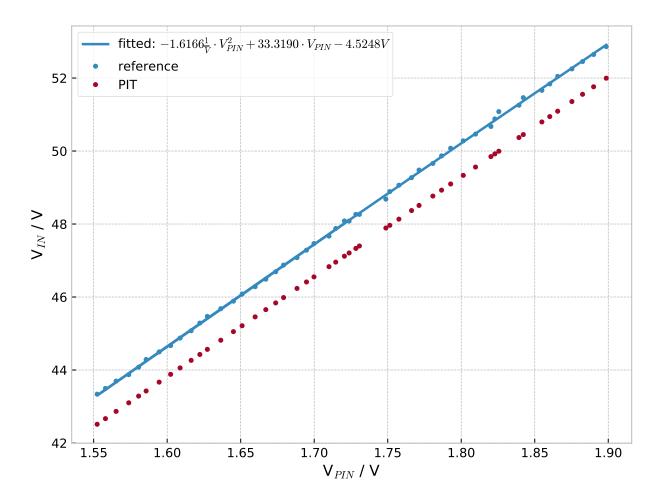


Figure 3.2: Calibration of input voltage, plotted are a external measurement and internal values, vs the recalculated pin voltage based on the internal value and used default function (default coefficients see Figure 4.2)

When looking at calibrating the input voltage (Figure 3.2), we can clearly see a relatively constant offset of ≈ 1 V. In Figure 3.2 a polynomial fit of 2nd degree¹ is done and its coefficients extracted (Figure 4.2.1, line 9). These coefficients not only show an offset, but also some deviation in the incline and curve from the default values.

¹A Fit of second degree will be used in the complete calibration process

9.6V Output

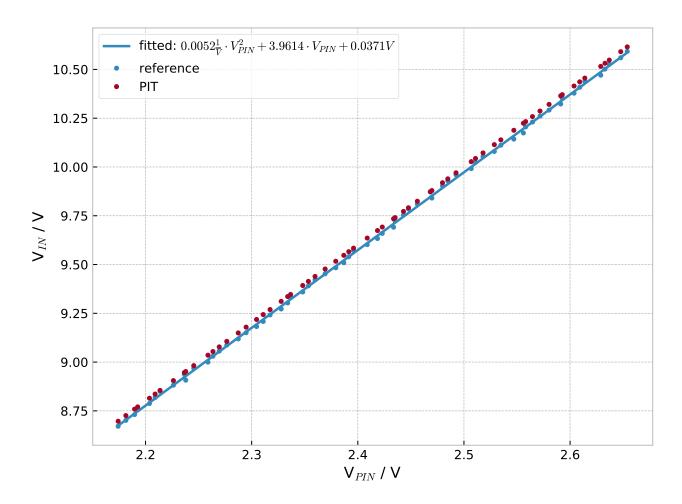


Figure 3.3: Calibration of 9.6V output Voltage, plotted are an external measurement and internal values vs the recalculated pin voltage based on the default coefficients (Figure 4.2)

The 9.6V Calibration, in contrast, shows only a slight deviation of the internal values and the reference measurement, which results in a list of coefficients (Figure 3.5, line 7), very similar to those set in the theoretical defaults.

This small difference is explained by the simple voltage division used as our circuitry, and no amplification, as for the input voltage circuit.

1.8V Output

The last Voltage to calibrate is divided into two domains, one for supplying the analog circuitry inside the wafer system, and one for the digital side. Each deliver between 1.5and 2.022V and each is settable by its own circuit (both as in Figure 2.3).

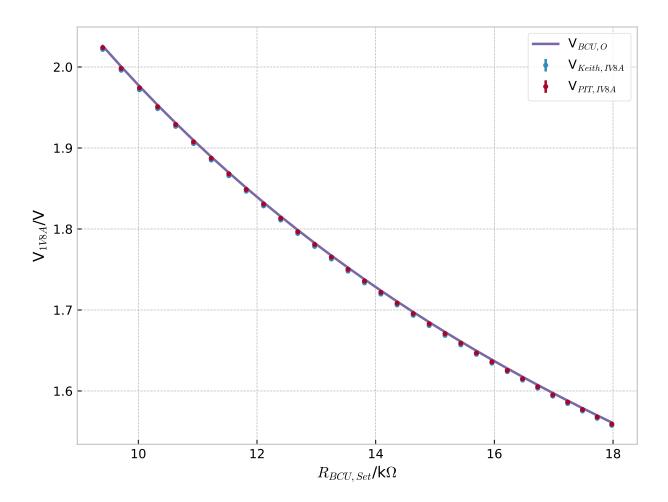


Figure 3.4: Calibration: analog 1.8V Output voltage, plotted are external measurement and internal values vs set resistance at the BCU Voltage Module.

Visualized in Figure 3.4 is the analog domains calibration, showing nearly no difference in board and reference measurements. Mostly due to direct connection between created voltage and the STM-Chips pin.

3.1.3 Currents

With now calibrated Voltages, the next step is to measure the behavior of the measuring circuits. Note that the 9.6V Output does in fact not have a include circuit for measuring its current draw, and that this number will be obtainable from all other (calibrated) measurements.

48V Input

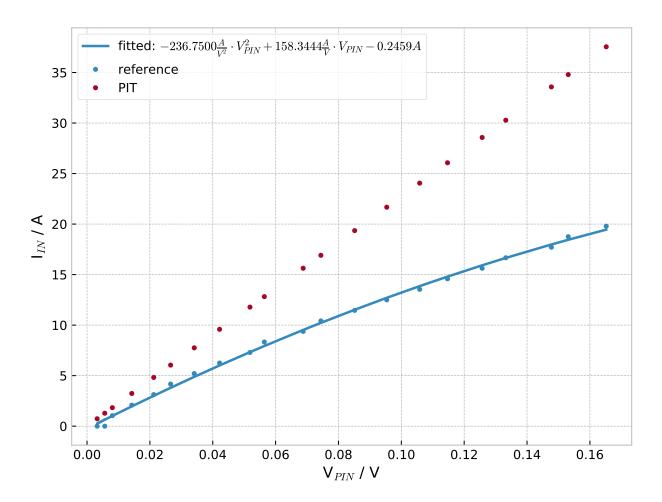


Figure 3.5: Calibration of input current adcs 21.06.2018

1.8V Output

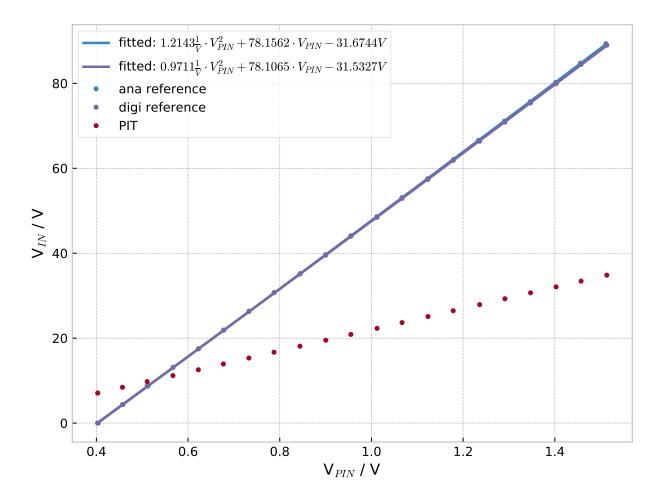


Figure 3.6: Pre Calibration Measurement of Output Current at the 1.8V Analog and Digital Terminal (2.7.2018)

3.2 1.8V Regulation

As Described beforehand the Output Voltages for both analog and digital can be adjusted to some degree and therefore we can compensate for the dropoff occuring between Powerlt Output Terminals and Reticles.

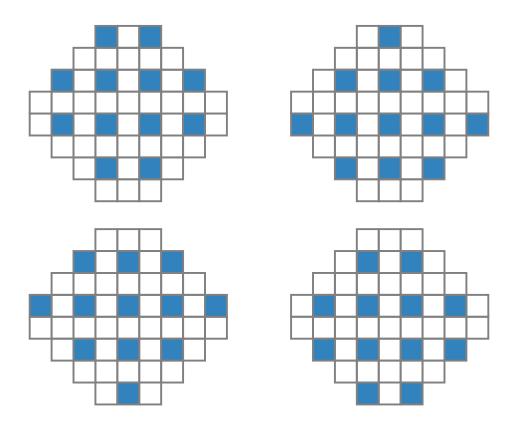


Figure 3.7: Used regular patterns for current tests on PowerWafer

3.2.1 Characterization of Dropoff

Wanting to observe and characterize the voltage drop, first the connections between Powerlt and Reticles can be measured with the in Figure 2.7 described connections, which in actuallity are the PowerlT Terminal and corresponding analog readout pin on a Analog readout board.

To use the PowerWfer for testing one of the patterns in Figure 3.7 will be used, each pattern has a aproximate currentdraw of 120A and will distribute heat and draw per terminal evenly.

In Figure 3.8 a single reticles (40) Voltage Dip for different Current Draws is visualized. A relatively linear trend and residuals of a trigonometric behavior can be observed (most likely the result of the inaccurately measureable current draw, which here is done inside the Powerlt).

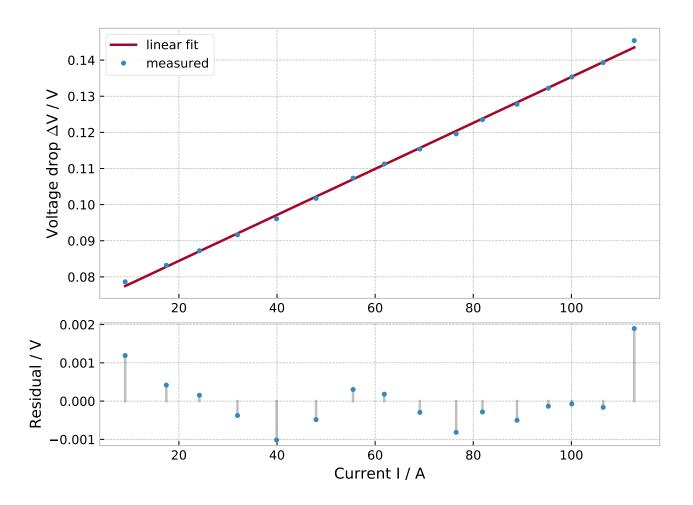


Figure 3.8: Voltage dip observed between Powerlt and HICANN, each point represents a state after enabling additional Reticles on the PowerWafer (right upper wafer in Figure 3.7)

Here a Voltage Drop vs. Current draw of the wafer shows a linear behavior and therefore can be regulated on basis of the current measurement done by on board Measurement circuit.

3.2.2 Numerical-Correction (Regulation)

The initial idea, to approach the correction of this dropoff is a Numerical: the SWRM (subsection 2.3.2) and its corresponding Equations can be applied here. Equation 2.11, which maps the measured output current to a corresponding potentiometer setting, requires the

Dropoff to be linear, which was observed.

To apply this approach, two assumptions need to be made:

- all reticles have the same current draw (already nmot accurate, see Figure 3.8)
- all reticles experience the same Voltage Dip (as observed for Reticle 40)

and the following four values are required, before a regulation can be attempted:

- ullet I_{ret} , the current draw of a single reticle,
- \bullet R_0 , the Resistance between Powerlt and FET,
- R_1 , the Resstance of a single Reticle
- ullet V_{off} , the wanted Voltage at a Reticle

To get a representative value of I_{ret} for use in the SWRM, the mean of all reticles current draw was taken (Figure 3.9):

$$I_{\text{ret,mean,corr}} = (9.9089 \pm 0.6049) \,\text{A}$$
 (3.1)

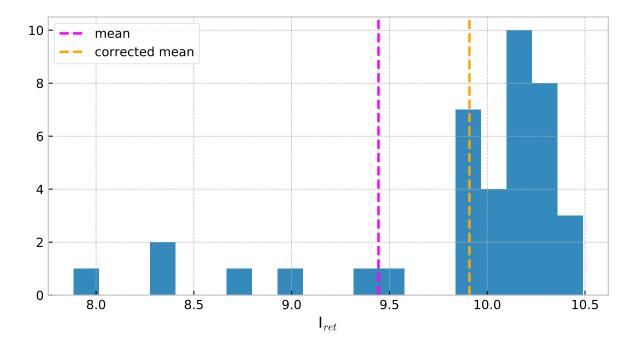


Figure 3.9: Distribution of analog current draw for all reticles on the PowerWafer (which were possible to measure \rightarrow section 3.3)

The Figure 3.9 was obtained by measuring the increase in current draw for each reticle, for each of the 4 patterns (Figure 3.7).

To obtain R_0 , the pattern in Figure 3.10 was used to take measurements for both the Neighborhood as well as the Farthest Reticles.

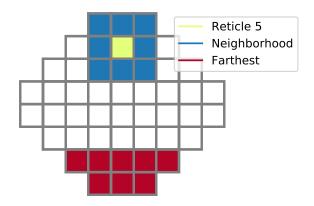


Figure 3.10: Reticles used to determine correlation between distance and Voltage Drop

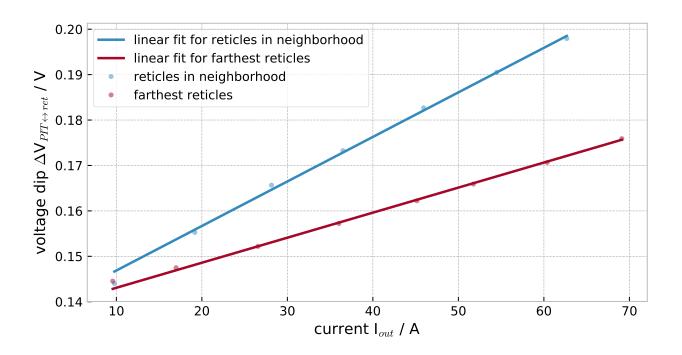


Figure 3.11: Voltage Dip vs current for both Reticles in direct neighborhood and farthest possible Reticles

From Figure 3.11 it is possible to see that the distance between reticles that are used gives different behavior of the Voltage Dip. Both Inclines happen to be the extreme cases, while either being completely uncorrelated, the case for farthest Reticles, or being directly correlated by their distance, here observable for the neighboring Reticles.

Therefore we obtain two values for R_0 :

$$R_{0,\text{neighbor}} = (7.1278 \pm 0.1567) \,\mathrm{m}\Omega$$
 (3.2)

$$R_{0,\text{farthest}} = (4.0079 \pm 0.0537) \,\text{m}\Omega$$
 (3.3)

from the same measurement it is also possible to extract R_1 by extrapolating to 0, which results in:

$$R_{1,\text{neighbor}} = (14.1708 \pm 0.1779) \,\mathrm{m}\Omega$$
 (3.4)

$$R_{1,\text{farthest}} = (14.2218 \pm 0.1503) \,\mathrm{m}\Omega$$
 (3.5)

here the values obtained are within error margin of each other. So applying these Values, the following behavior for regulation can be visualized:

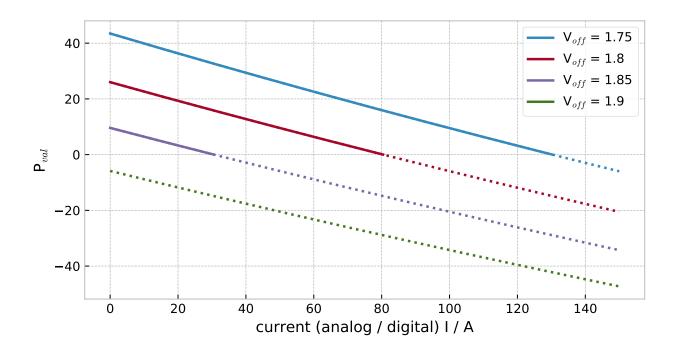


Figure 3.12: possible P_{val} curves after SWRM, dotted lines represent not achievable values

The in Figure 3.12 visualized values show the theoretical P_{val} for the corresponding Current, while all dotted parts depict the values wich would be needed to achieve full correction at the Reticle level. Note that the 1.8V regulation, should fail at about 80A of current draw.

Now that the SWRM is appliable, what about the DWRM, which removes the assuption of a equal Voltage Dip per Reticle, applying an offset to the initially observed Voltage of each Reticle.

To account for that, the Voltage Dip per Reticle, in a simgle Reticle power state, was observed:

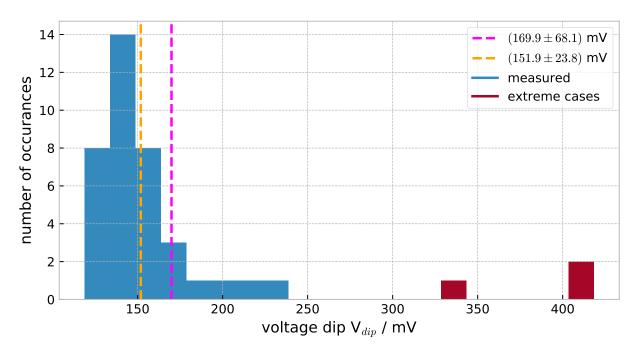


Figure 3.13: initially observed Voltage Dip, Red values are ignored for corrected mean

and a mean of:

$$V_{\rm dip,mean,corrected} = (151.8811 \pm 23.8138) \,\text{mV}$$
 (3.6)

can be observed.

Figure 3.14 shows how those Voltages are Distributed over the complete PowerWafer. All white Reticles are not measurable, and those colored in Red and Yellow are the outliers in Figure 3.13. Note that in a deployed, working, Wafer System inside BrainScaleS the iddle two Reticles are not used and also give grounds to ignoring the outliers.

This results in a distribution, which when combined with the spread of R_0 from Figure 3.11, gives an approximate range for all Reticles Voltage Dip at a given Current Draw (Figure 3.15).

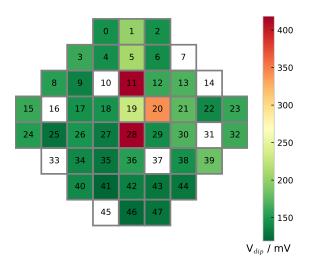


Figure 3.14: V_{dip} Distribution over full Power Wafer; White have no measurement; Red an Orange are marked red in Figure 3.13

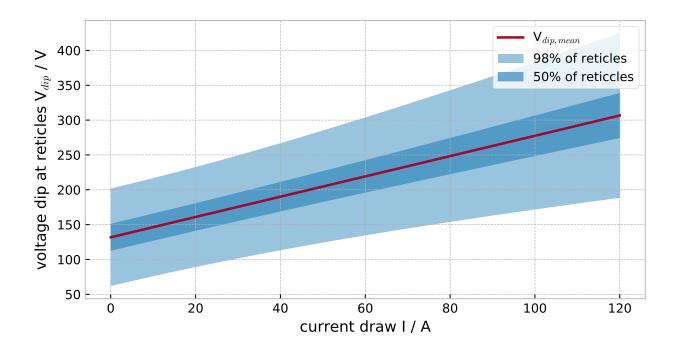


Figure 3.15: Expermentally obtained Voltage Ranges in which most Reticles Voltage Dip will lie, this does not include outliers

3.3 Pitfalls

4 Results

This Chapter summaizes all of the resulting Workflow that has been developed during this Bachelor Thesis Work. Mainly the Firmware Changes compared to the state at wich it was left off after the previously taken Internship [3]

4.1 Firmware

The Powerlt Firmware was updated to allow for the Calibration Procedure (described in 4.2) and the Rgulation of its 1.8V output. That resulted in a new Version of the I2C Protocol between the Monitoring System and Powerlts.

4.1.1 PI2CProto v2

The new Commmunication protocoll is based on the old one, and while the from the Host send Commands are compatible with version 1 the returned Message is not. And just like in the old Version a Master can send a message to the Powerlt with the in the command_t struct described structure:

Here the <CMD> can be CMD_SET for setting a value in the corresponding table (fig. 4.1), using <optional_data0> as address and <optional_data1> as value.

Reading a number of bytes from the table can be accomplished with CMD_READ, giving the address to start and number of bytes in that order.

While reading the complete Table is done with the CMD_READALL command.

THe <crc> byte is the CRC8 value of all following bytes inside command_t

4.1.2 I2C mapped Register-Table

When sending or reading values to or from the Powerlt, the address required is one of the 152 bytes documented in this table.

addr	name	type	size	perm
0×00	onmask	byte	1	rw
0×01	offmask	byte	1	rw
0×02	anapot	9bit	2	rw
0×04	digipot	9bit	2	rw
0×06	polyFit.V48	float arr	12	rw
0×12	polyFit.I48	float arr	12	rw
0×1e	polyFit.V8	float arr	12	rw
0x2a	polyFit.V18	float arr	12	rw
0×36	polyFit.I18	float arr	12	rw
0×42	polyFit.T	float arr	12	rw
0x4e	sampleTicks	byte	1	rw
0x4f	V_out	float	4	rw
0x53	TEMP_SENSOR	float	4	r
0x57	EXT_AIN	float	4	r
0×5b	MONITOR_48V	float	4	r
0x5f	MONITOR_48I	float	4	r
0×63	MONITOR_8VBUS	float	4	r
0×67	MONITOR_8IBUS	float	4	r
0x6b	MONITOR_8V_0	float	4	r
0x6f	MONITOR_8V_1	float	4	r
0×73	MONITOR_8V_2	float	4	r
0×77	MONITOR_8V_3	float	4	r
0x7b	VDD_1V8_ANA	float	4	r
0x7f	VDD_1V8_IOUT_ANA	float	4	r
0x83	VDD_1V8_DIGI	float	4	r
0x87	VDD_1V8_IOUT_DIGI	float	4	r
0x8b	CommitHash	float	4	S
0x8f	CommitDirtyFlag	byte	1	S
0×90	STM32UUID	96bit	12	S

Figure 4.1: memory mapping of the packed struct moved over i2c, addr is the address to use, type is the c++ type, size is in bytes and perm denotes read-writability. writability

4.2 Calibration

One of the goals of this Bachelor Thesis is to provide anyone required to calibrate a Powerlt Board with a comprehensive guide of, and inside into this process.

```
id: '0x280029000F51333332343638'
name: B05
poly18iana: [-31.5155, 78.516, -0.0688]
poly18idigi: [-31.3536, 78.3701, -0.196]
poly18i: [-31.4396, 78.443, -0.1324]
poly48i: [-0.1765, 153.0021, -204.1858]
poly10v: [0.6348, 3.459, 0.1118]
poly48v: [-4.5248, 33.3195, -1.6167]
poly18v: [0.0234, 0.9728, 0.0072]
```

4.2.1 Calibration-Table

Of important note is that al calibration values of each Powerlt can be mapped via the naming and unid scheme provided either by the corresponding stickers or the STM32-Chips internal unid (accessible through address 0x8c, see figure 4.1). There now also exists a global calibration Database, which will be loaded by the system on startup.

An example entry for each Powerlt entry looks like figure 4.2

```
Figure 4.2: example entry of pitdb.yaml

---

uuid: 'default'
name: 'Bxx'
poly18i: [-3.0, 25.0, 0.0]
poly48i: [0.0, 227.27, 0.0]
poly10v: [0.0, 4.0, 0.0]
poly18v: [0.0, 1.0, 0.0]
poly48v: [0.0, 27.386, 0.0]
```

4.2.2 How to calibrate a Powerlt Board

The Calibration process is based on the PItSTOP Python scripts¹. These are split into server and aggregator. While the Server is handling the translation between raw I²C data, and the JSON formatted result, the Aggregator takes this JSON and calculates a calibration.

Using the script any one of the following Values can be tested and calibrated:

- Input Voltage (pitstop.Aggregator.test_v_48())
- Input Current (pitstop.Aggregator.test_i_48())

¹ PltSTOP Repo

- 9.6V Output Voltage (pitstop.Aggregator.test_v_10())
- 1.8V Output Voltage (pitstop.Aggregator.test_v_18())
- 1.8V Output Current (pitstop.Aggregator.test_i_18())

Setting up the Test Environment

The simplest way to setup your environment consists of cloning the PItSTOP Project onto your Client:

```
> git clone https://url.to.pitstop
```

then substituting the rsync target:

```
all:
rsync --progress ./*.py /remote.url/
```

, to be your server (should be a RaspberyyPi connected to the Powerlt)

Running a Test

Runnig the test requires the following commands Serverside:

```
> python server.py
```

Clientside:

```
> python aggregator.py
```

Now just following the instructions given, the selected test can be run:

4.3 Regulation

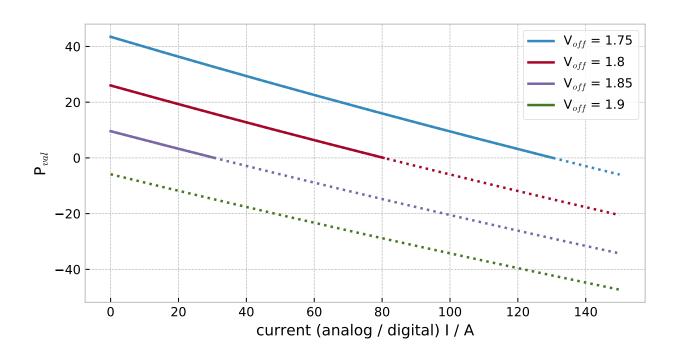


Figure 4.3: theretical potentiomete settings for meausured current

5 Outlook

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